

10/663,741.

NOFCE

Docket No.: M4065.0656/P656
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Terry L. Gilton

Patent No.: 6,903,361

Issued: June 7, 2005

For: NON-VOLATILE MEMORY STRUCTURE

Certificate
DEC 19 2006
of Correction

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322 & 1.323**

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the Drawings, Applicant's Submission of Formal Drawings, dated December 18, 2003, was not included in the printed patent by the PTO. Exhibit A (attached) is a copy of that Submission with drawings to be substituted for the rough drawings that are used in the patent.

In the U.S. Patent Documents portion of the References Cited section, the following is to be corrected:

2002/0000668 A1 1/2002 Kozicki et al. should read

DSMDB-2183254v01

DEC 21 2006

2002/0000666 A1 1/2002 Kozicki et al.

In the Specification, Applicant made the following errors to be corrected:

Column 5:

Line 48, "deposition an" should read --deposition of an--; and

Line 61, "increase" should read --increases--.

Column 6:

Line 4, "increase" should read --increases--; and

Line 5, "decrease" should read --decreases--.

Column 7:

Line 47, "include" should read --includes--.

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Line 4, "an local" should read --a local--;

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Line 9, "via to the" should read --via the--; and

Line 12, "to one additional" should read --to additional--.

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In the Other Publications portion of the References Cited section, the PTO made the following errors to be corrected:

"Yoji Kawamoto et al., "Ionic Conduction in As_2S_3 - Ag_2S , GeS_2 - GeS_2 - GeS - Ag_2S and P_2S_6 - Ag_2S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404."

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"El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of $\text{Ag}_{2-x}\text{Se}_{1+x/n}$ -Si diodes, Thin Solid Films 110 (1983) 107-113."

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"Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828."

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"Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851."

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--Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.--.

Also in Other Publications, Applicant made the following errors to be corrected:

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

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Should read

--McHardy, et al., The dissolution of metals in amorphous chalcogenides and the effect of electrons and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--.

The errors were both found in the application as filed by Applicant and made by the PTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0656/P656.

Dated: December 14, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499

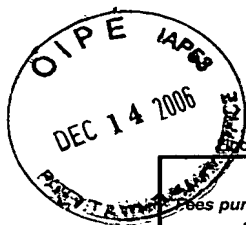
DICKSTEIN SHAPIRO LLP

1825 Eye Street, NW

Washington, DC 20006-5403

(202) 420-2200

Attorneys for Applicant



Effective on 12/08/2004. Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).		Complete if Known	
FEE TRANSMITTAL For FY 2006		Application Number	Patent#: 6,903,361
		Filing Date	Issued: June 7, 2005
		First Named Inventor	Terry L. Gilton
		Examiner Name	C. Q. Nguyen
		Art Unit	2811
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27	TOTAL AMOUNT OF PAYMENT	(\$)	100.00
		Attorney Docket No.	M4065.0656/P656

METHOD OF PAYMENT (check all that apply)	
<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card
<input type="checkbox"/> Money Order	<input type="checkbox"/> None
<input type="checkbox"/> Other (please identify): _____	
<input checked="" type="checkbox"/> Deposit Account	Deposit Account Number: <u>04-1073</u> Deposit Account Name: <u>Dickstein Shapiro LLP</u>
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)	
<input type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayments of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

FEE CALCULATION							
1. BASIC FILING, SEARCH, AND EXAMINATION FEES							
	FILING FEES		SEARCH FEES		EXAMINATION FEES		
		Small Entity		Small Entity		Small Entity	
Application Type	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fees Paid (\$)
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	
2. EXCESS CLAIM FEES							
Fee Description						Small Entity	
						Fee (\$)	Fee (\$)
Each claim over 20 (including Reissues)						50	25
Each independent claim over 3 (including Reissues)						200	100
Multiple dependent claims						360	180
Total Claims	Extra Claims	Fee (\$)	Fee Paid (\$)		Multiple Dependent Claims		
		x	=		Fee (\$)	Fee Paid (\$)	
HP = highest number of total claims paid for, if greater than 20.							
Indep. Claims	Extra Claims	Fee (\$)	Fee Paid (\$)				
		x	=				
HP = highest number of independent claims paid for, if greater than 3.							
3. APPLICATION SIZE FEE							
If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).							
Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof	Fee (\$)	Fee Paid (\$)			
	- 100 =	/50	(round up to a whole number) x	=			
4. OTHER FEE(S)							
Non-English Specification, \$130 fee (no small entity discount)							Fees Paid (\$)
Other (e.g., late filing surcharge): 1811 Certificate of correction							100.00

SUBMITTED BY			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 420-2232
		Date	December 14, 2006

DEC 21 2006

Exhibit A

Inventor: Terry L. Gilton

Atty Docket No.: M4065.0656/P656

Application No.: 10/663,741

Filing Date: September 17, 2003

Title: NON-VOLATILE MEMORY STRUCTURE

Documents Filed:

Submission of Formal Drawings (1 page)

9 drawings (9 sheets)

Information Disclosure Statement (20 pages), PTO SB/08 (11 pages) with 1 box of references

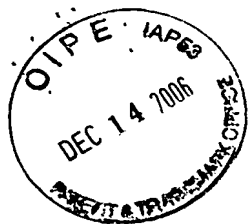
Via: PTO DAILY RUN

Sender's Initials: TJD/CSC/cdl

Date: December 18, 2003



12-18-03



Docket No.: M4065.0656/P656
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Terry L. Gilton

Application No.: 10/663,741

Filed: September 17, 2003

Art Unit: N/A

For: NON-VOLATILE MEMORY STRUCTURE

Examiner: Not Yet Assigned

SUBMISSION OF FORMAL DRAWINGS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Submitted herewith is one set (nine sheets, nine figures) of formal drawings for filing in the above-identified patent application. Kindly substitute the enclosed formal drawings for the informal drawings submitted with the originally filed application.

Dated: December 18, 2003

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Christopher S. Chow

Registration No.: 46,493

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW
Washington, DC 20037-1526
(202) 785-9700
Attorneys for Applicant

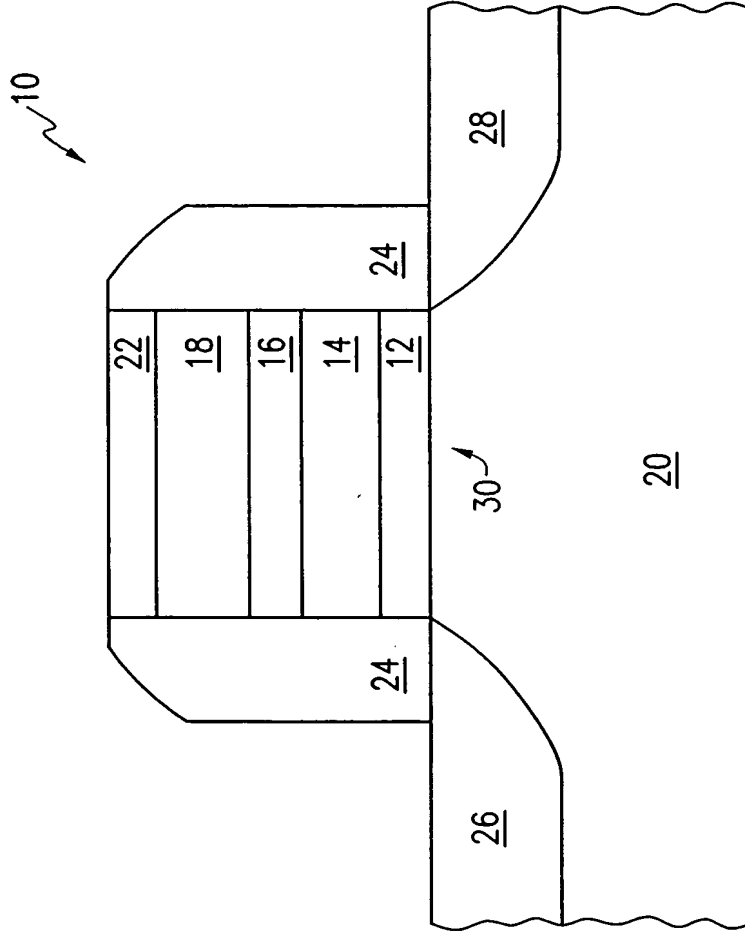


FIG. 1 (PRIOR ART)

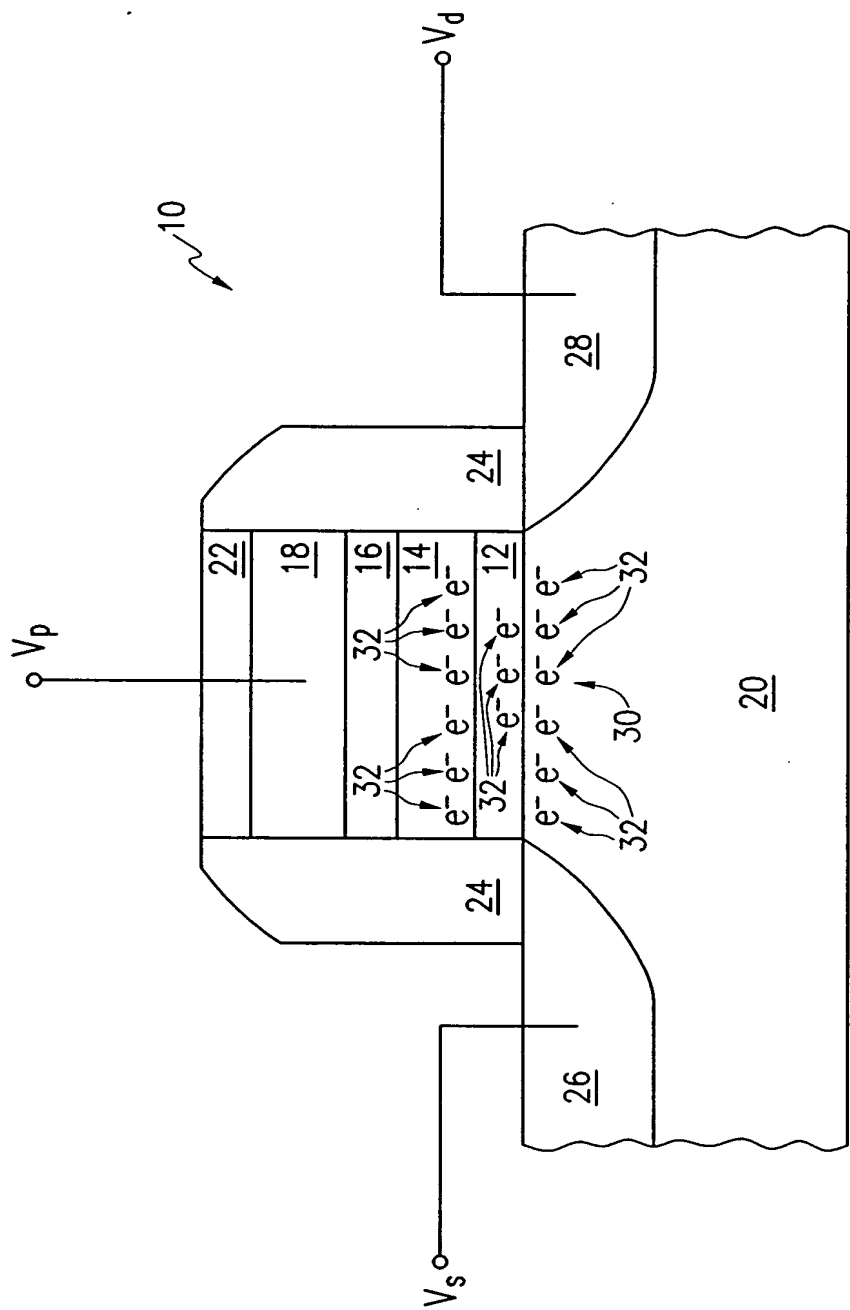


FIG. 2 (PRIOR ART)

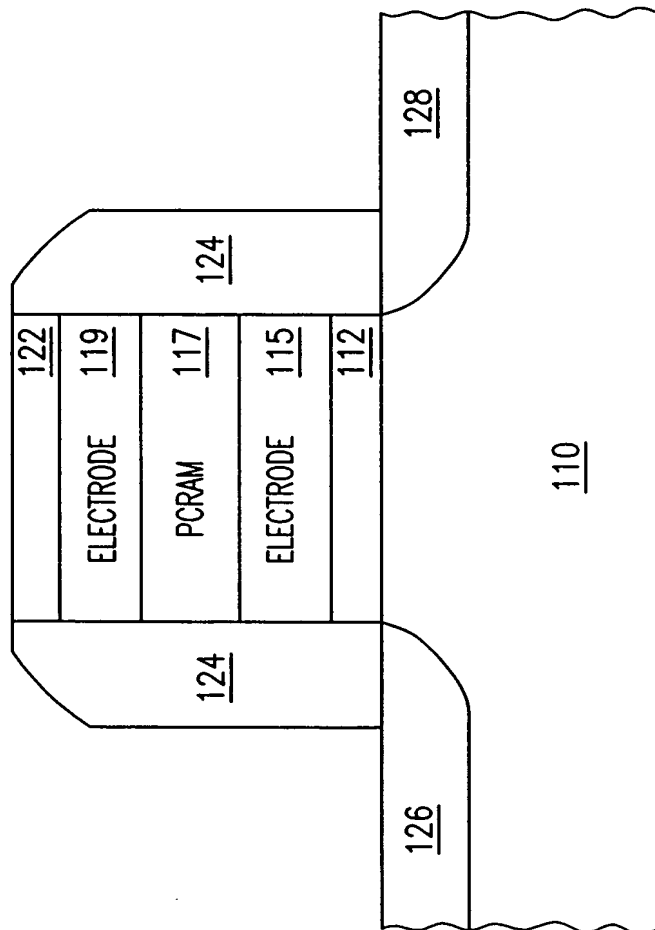


FIG. 3

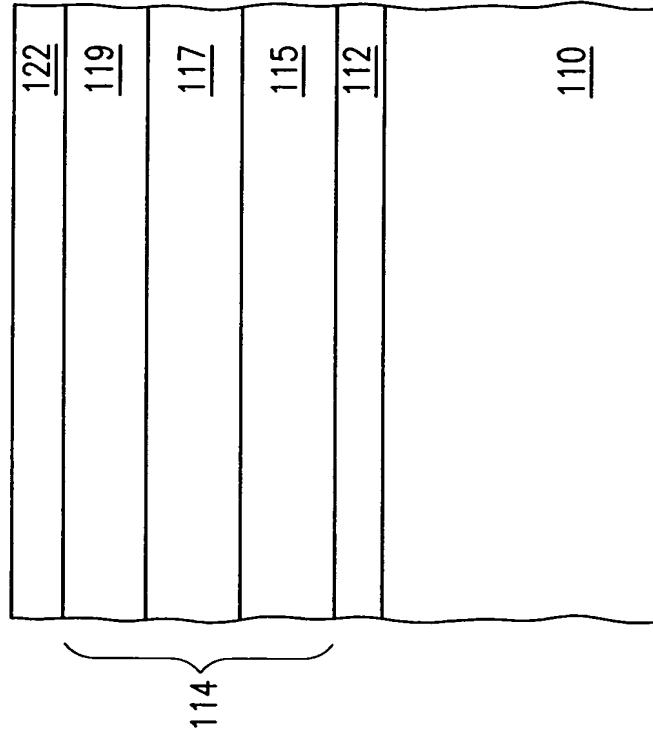


FIG. 4

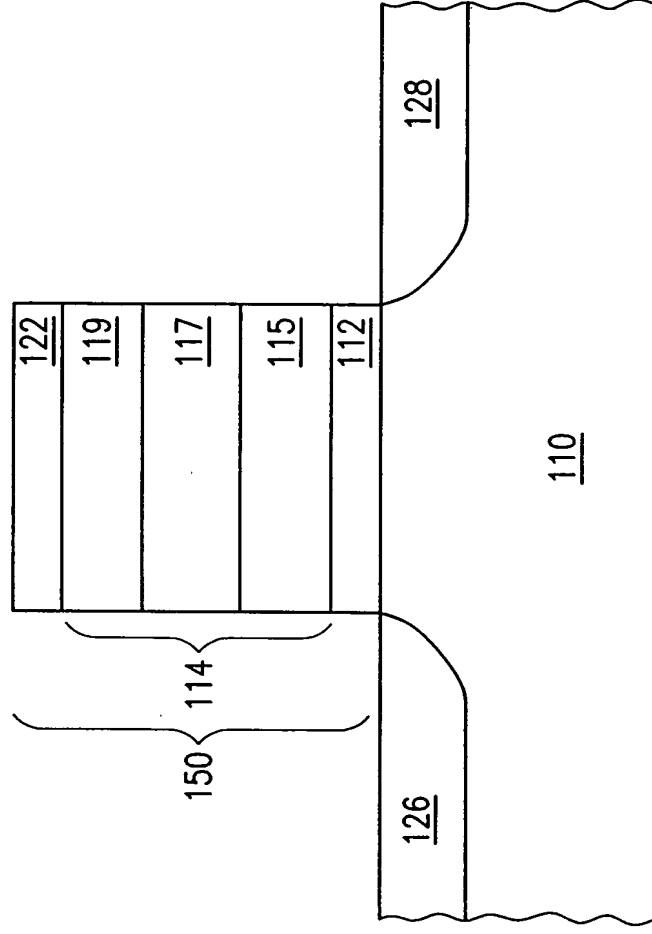
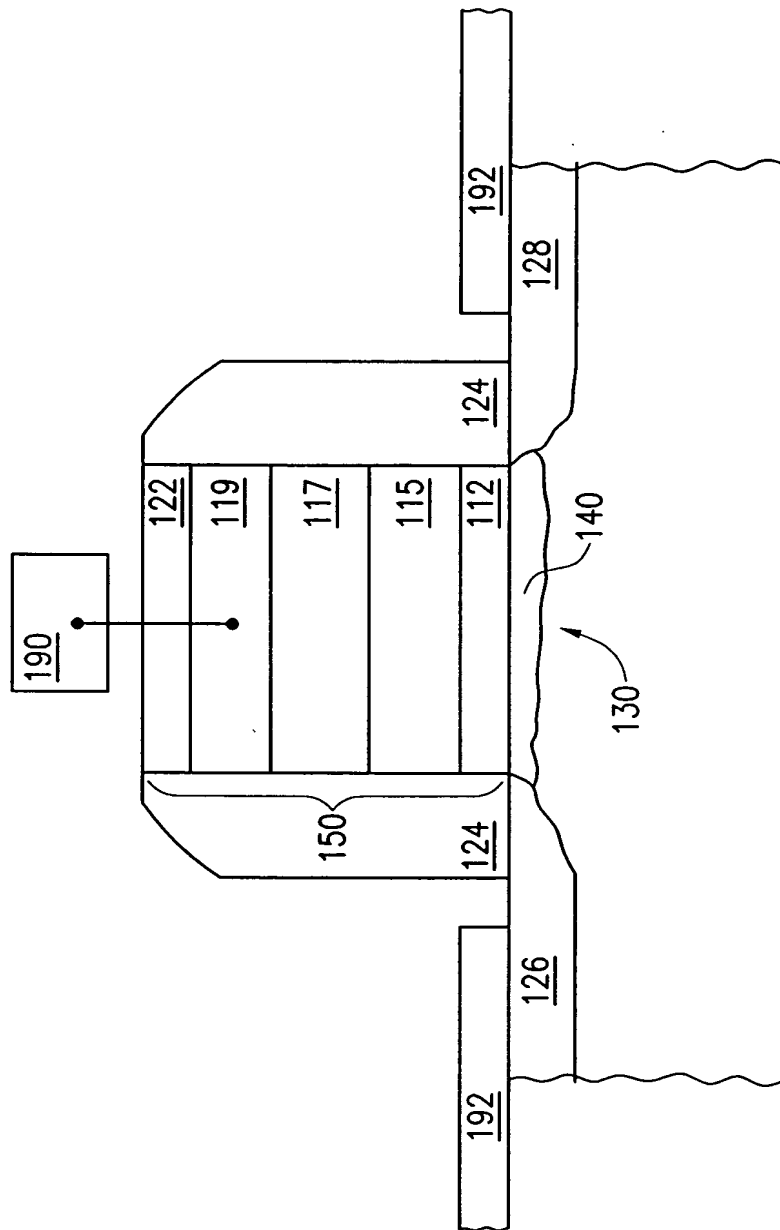


FIG. 5



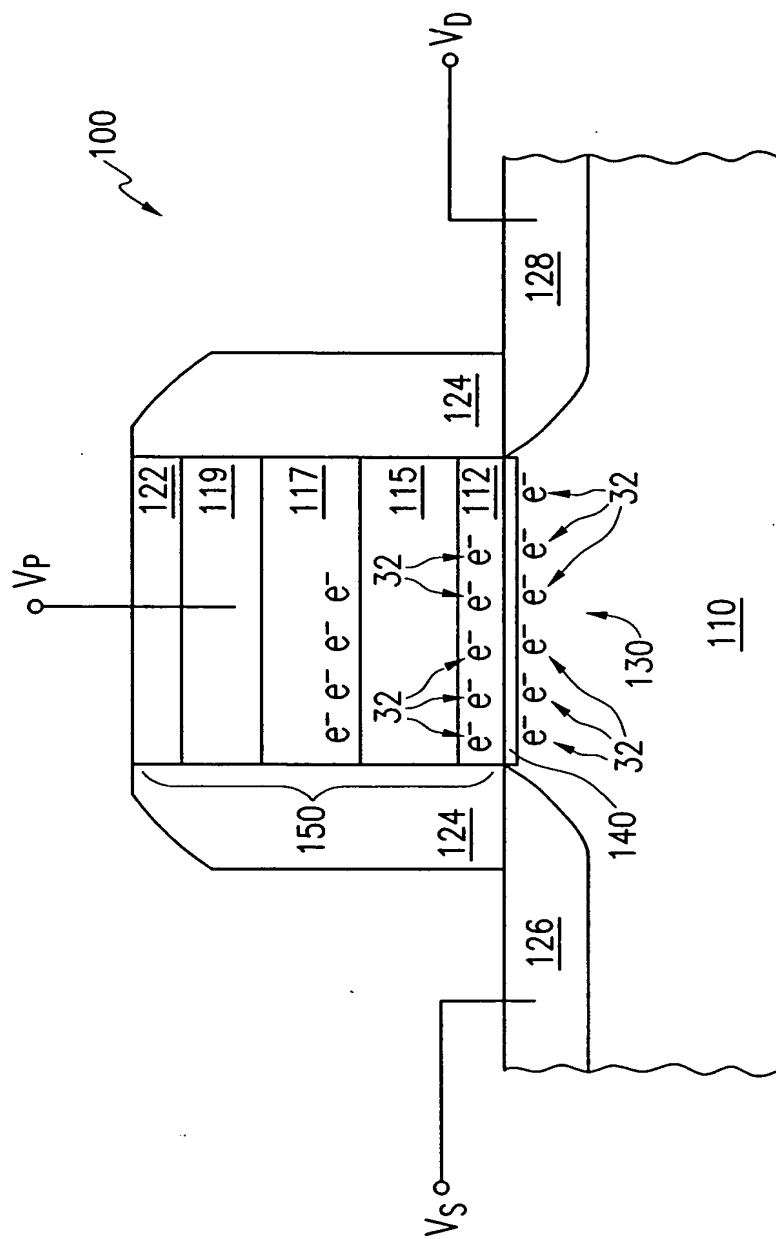


FIG. 7

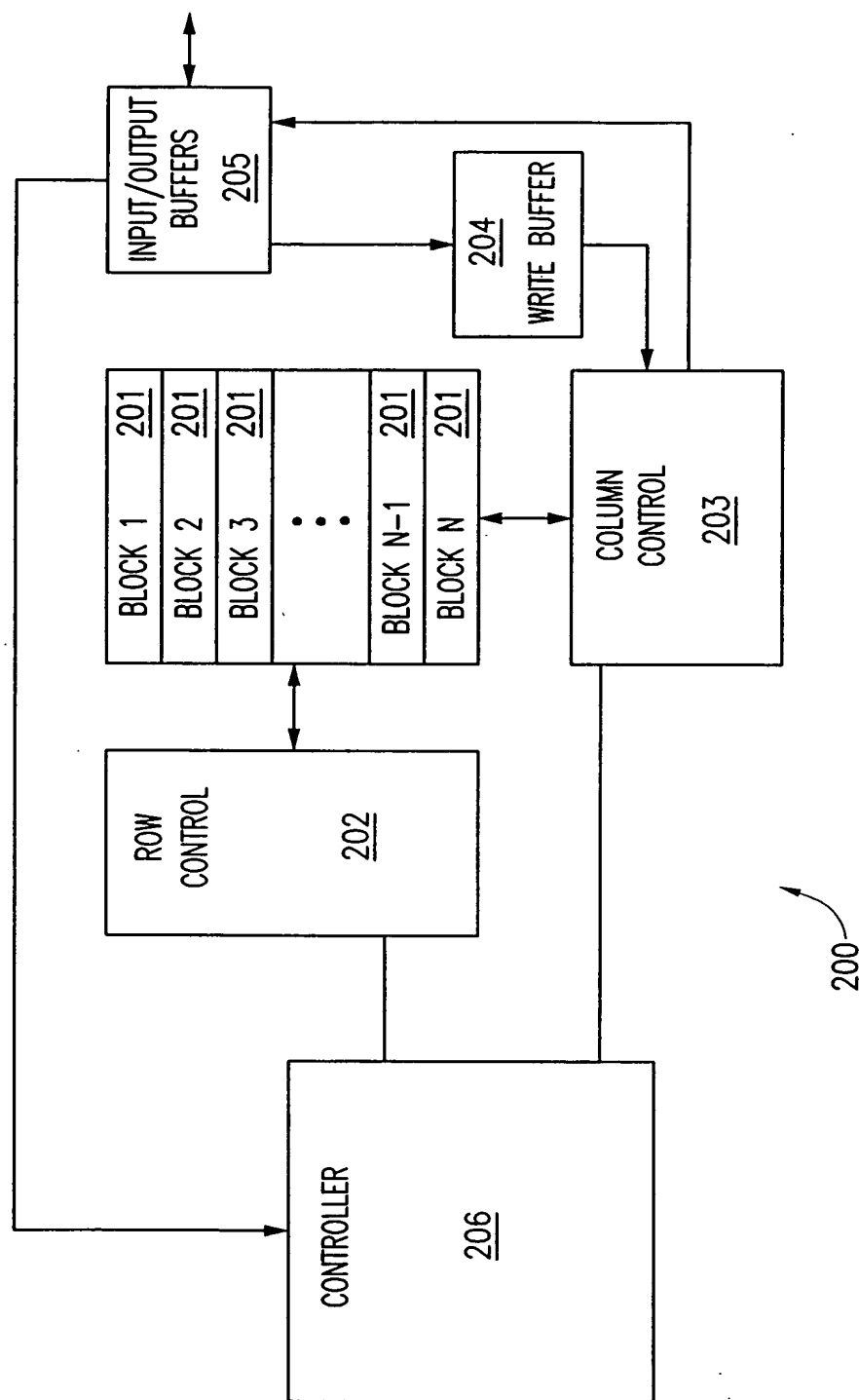
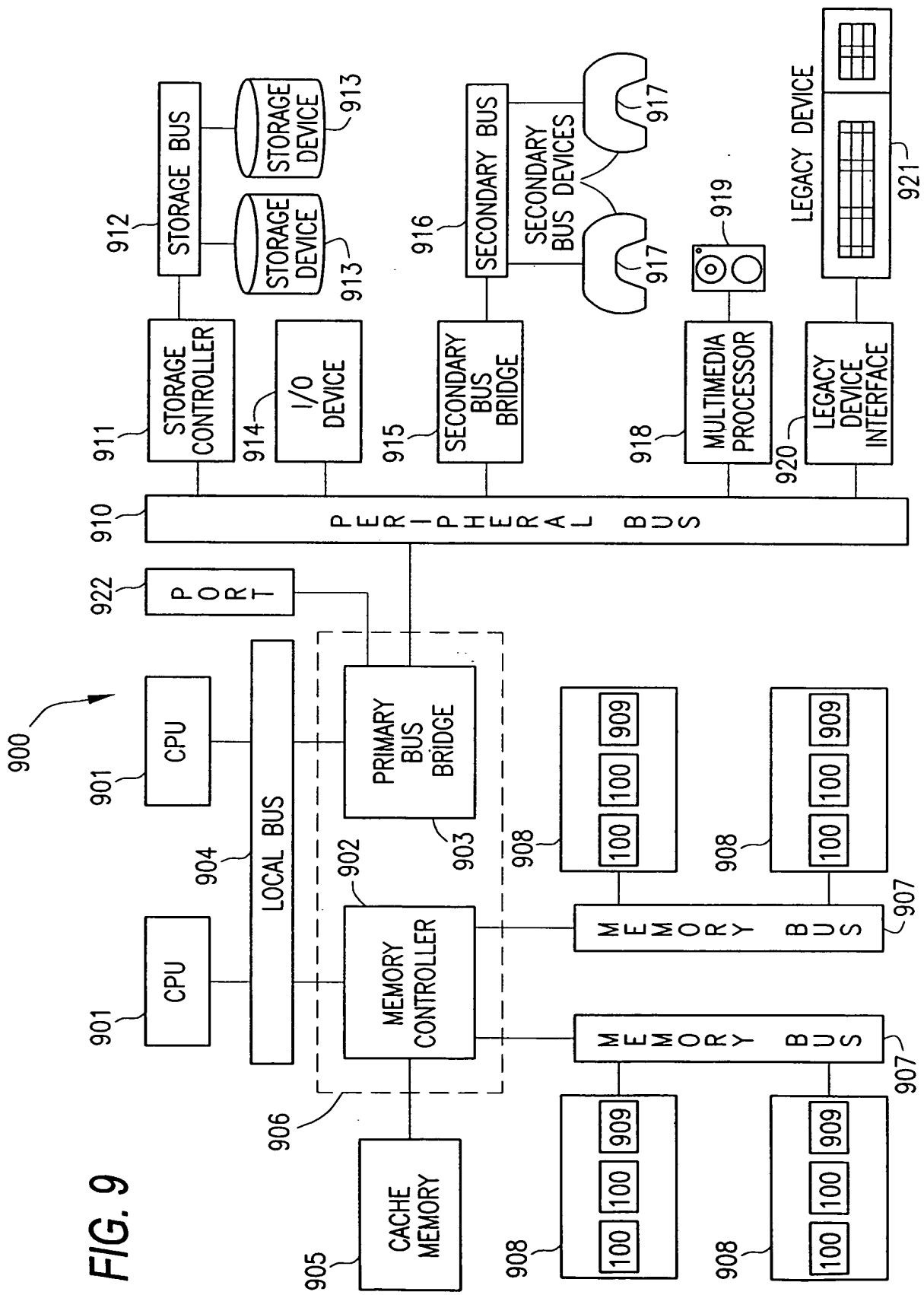


FIG. 8

FIG. 9



**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 3

PATENT NO. : 6,903,361
APPLICATION NO. : 10/663,741
ISSUE DATE : June 7, 2005
INVENTOR : Terry L. Gilton

It is certified that an errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Drawings, substitute the attached set of drawings for those that are in the patent.

In the U.S. Patent Documents portion of the References Cited section, the following is corrected:

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Column 7:

Line 47, "include" should read --includes--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO LLP
1825 Eye Street, NW
Washington, DC 20006-5403

Column 8:

Line 4, "an local" should read --a local--;

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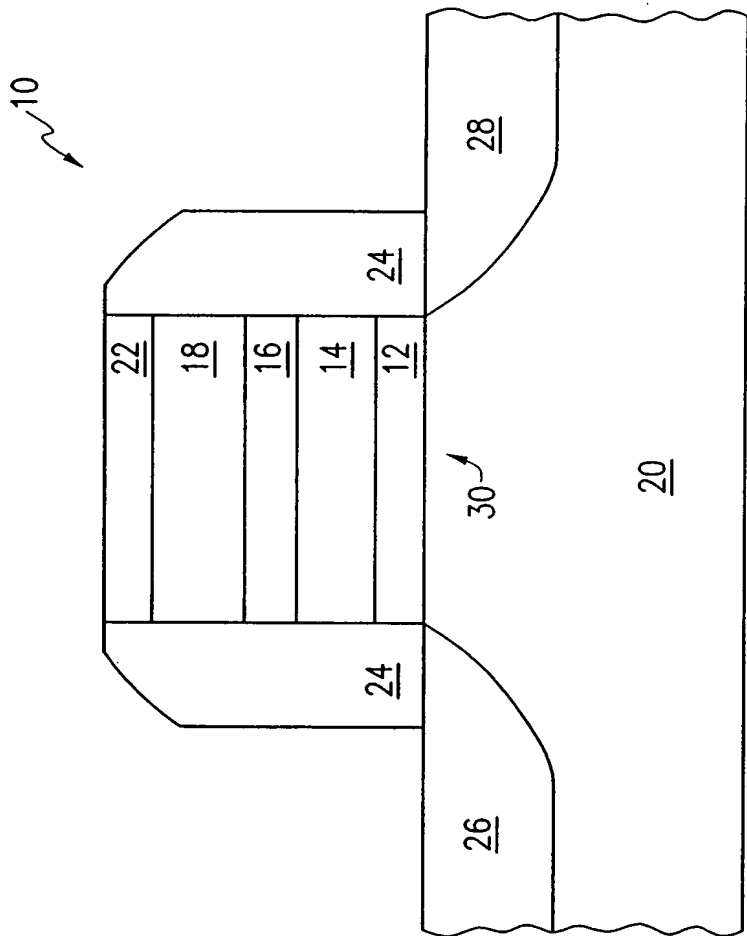


FIG. 1 (PRIOR ART)



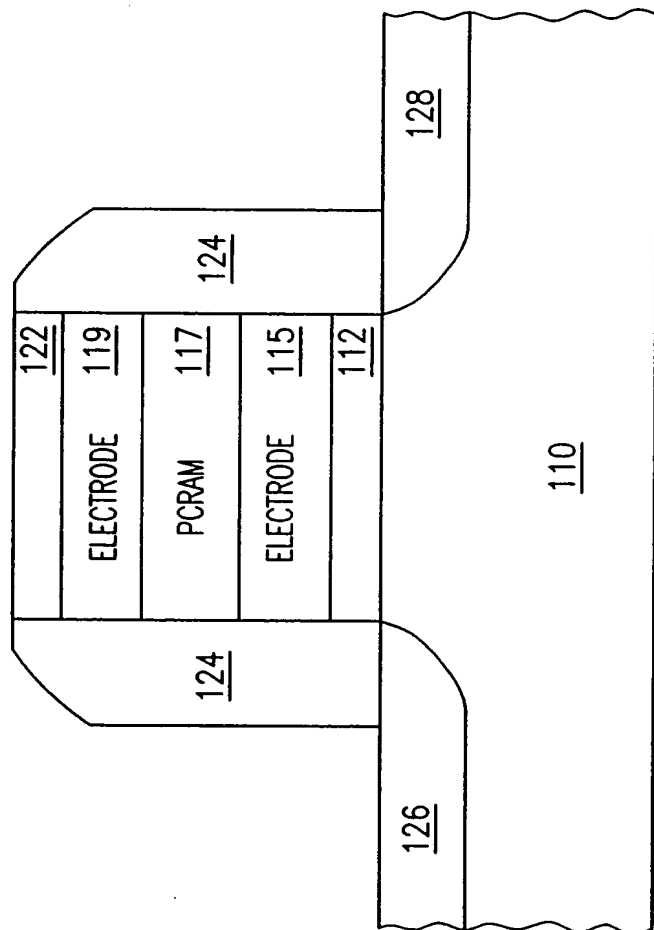


FIG. 3

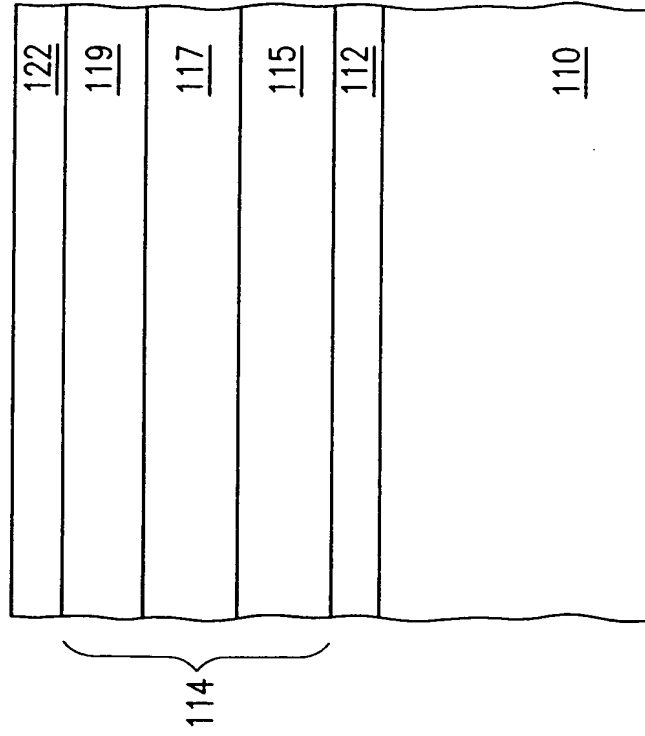


FIG. 4

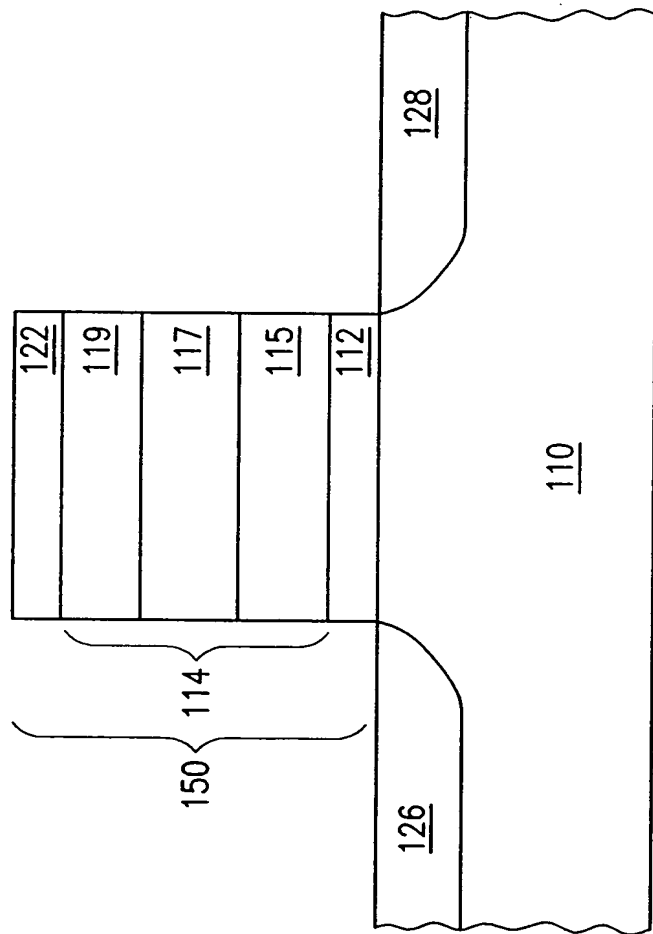


FIG. 5

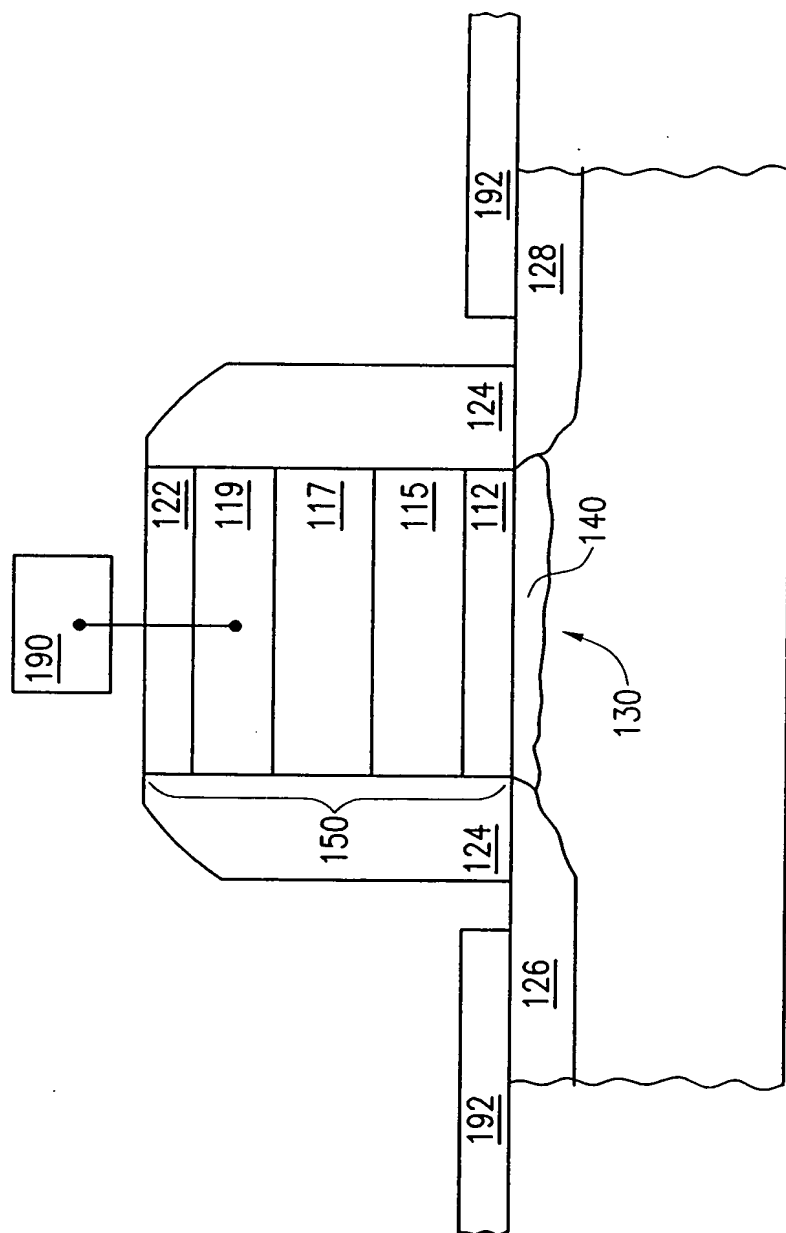


FIG. 6



FIG. 7

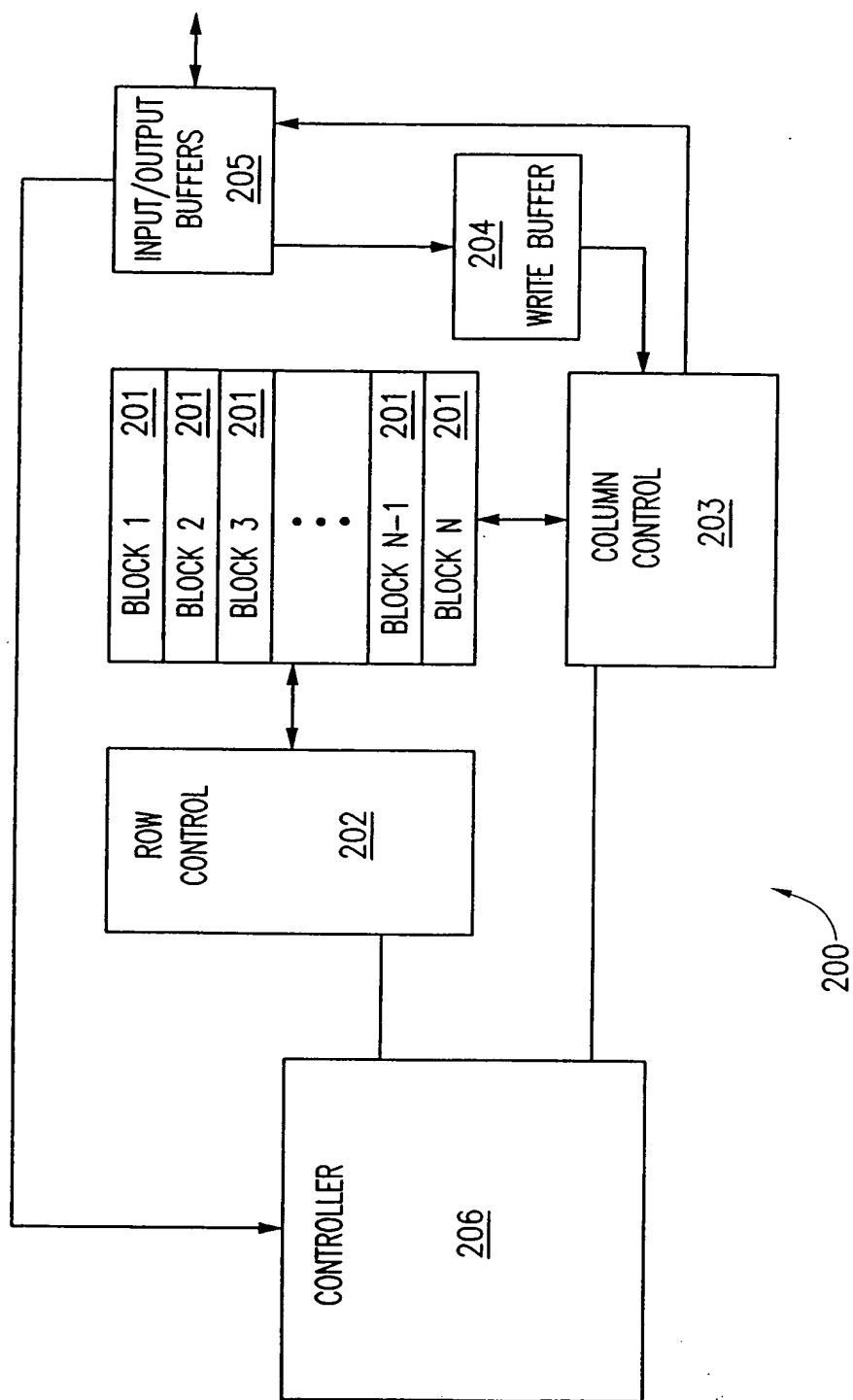


FIG. 8

FIG. 9

